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View Online at https://aerobasegroup.com/nsn/5961-01-285-0435

view Online at http	s.//aerobasegroup.com/nsi//3901-01-263-0435
Inclosure Materia	l:
Glass	
Overall Length:	
0.357 inches	
Terminal Length:	
1.625 inches	
Overall Diameter:	
0.235 inches	
Function For Whi	ch Designed:
Transient suppress	sor
Joint Electronic D	Device Engineering Council/jedec/case Outline Designation:
Do-13	
Electrode Internal	Ily-electrically Connected To Case:
Collector	
Mounting Method	:
Terminal	
Features Provided	d:
Hermetically sealed	d case and quality assurance level tx
Semiconductor M	aterial:
Silicon	
Voltage Rating In	Volts Per Characteristic:
179.0 breakdown	voltage, dc
Voltage Tolerance	e In Percent:
-5.0/+5.0	
Current Rating Pe	er Characteristic:
5.00 microamperes	s forward current, average peak
Power Rating Per	Characteristic:
1.0 watts small-sig	nal input power, common-collector major
Maximum Operati	ing Tempurature Per Measurement Point:
175.0 degrees cels	sius ambient air
Test Data Docum	ent:
81349-mil-s-19500	specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes c	commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and	performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type An	d Quantity:
2 uninsulated wire	lead
Specification Data	a:
81349-mil-s-19500	/500 government specification
Shelf Life:	
N/a	
Unit Of Measure:	
 Demilitarization:	
No	

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